

V _{CES}	650V
I _{C(100°C)}	21A
V _{CE(sat) (Typ.)}	1.6V@I _C =50A
P _D	72W

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Pb free Lead Plating ; RoHS Compliant

Applications

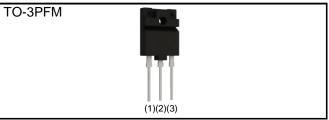
PFC

UPS

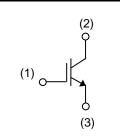
Power Conditioner

IH

Outline



Inner Circuit





Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Tuno	Tape Width (mm)	-
Туре	Basic Ordering Unit (pcs)	450
	Packing Code	C11
	Marking	RGTH00TK65

•Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	650	V
Gate - Emitter Voltage		V _{GES}	±30	V
Collector Current	$T_{\rm C} = 25^{\circ}{\rm C}$	Ι _C	35	А
Collector Current	$T_{\rm C} = 100^{\circ}{\rm C}$	Ι _C	21	А
Pulsed Collector Current		I _{CP} ^{*1}	200	А
Power Dissinction	$T_{\rm C} = 25^{\circ}{\rm C}$	P _D	72	W
Power Dissipation	$T_{\rm C} = 100^{\circ}{\rm C}$	P _D	36	W
Operating Junction Temperature		Tj	-40 to +175	°C
Storage Temperature		T _{stg}	–55 to +175	°C

*1 Pulse width limited by T_{jmax.}

Thermal Resistance

Parameter	Symbol	Values			Unit
Parameter	Зуший	Min.	Тур.	Max.	Unit
Thermal Resistance IGBT Junction - Case	$R_{\theta(j\text{-}c)}$	-	-	2.07	°C/W

•IGBT Electrical Characteristics (at $T_j = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Conditions	Values			Linit
Faranieler	Symbol Conditions		Min.	Тур.	Max.	Unit
Collector - Emitter Breakdown Voltage	BV _{CES}	I _C = 10μΑ, V _{GE} = 0V	650	-	-	V
Collector Cut - off Current	I _{CES}	V _{CE} = 650V, V _{GE} = 0V	-	-	10	μA
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30 V, V_{CE} = 0 V$	-	-	±200	nA
Gate - Emitter Threshold Voltage	V _{GE(th)}	V _{CE} = 5V, I _C = 34.7mA	4.5	5.5	6.5	V
Collector - Emitter Saturation Voltage	V _{CE(sat)}	$I_{C} = 50A, V_{GE} = 15V$ $T_{j} = 25^{\circ}C$ $T_{j} = 175^{\circ}C$	-	1.6 2.1	2.1 -	V

•IGBT Electrical Characteristics (at $T_j = 25^{\circ}C$ unless otherwise specified)

Deremeter	Symbol	Conditions	Values			l la it
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	C _{ies}	V _{CE} = 30V	-	2740	-	
Output Capacitance	C _{oes}	$V_{GE} = 0V$	-	106	-	pF
Reverse Transfer Capacitance	C _{res}	f = 1MHz	-	43	-	
Total Gate Charge	Qg	V _{CE} = 300V	-	94	-	
Gate - Emitter Charge	Q _{ge}	I _C = 50A	-	22	-	nC
Gate - Collector Charge	Q _{gc}	V _{GE} = 15V	-	31	-	
Turn - on Delay Time	t _{d(on)}	$I_{\rm C} = 50$ A, $V_{\rm CC} = 400$ V	-	39	-	
Rise Time	t _r	$V_{GE} = 15V, R_{G} = 10\Omega$	-	63	-	
Turn - off Delay Time	t _{d(off)}	$T_j = 25^{\circ}C$	-	143	-	ns
Fall Time	t _f	Inductive Load	-	50	-	
Turn - on Delay Time	t _{d(on)}	$I_{\rm C} = 50$ A, $V_{\rm CC} = 400$ V	-	39	-	
Rise Time	t _r	$V_{GE} = 15V, R_{G} = 10\Omega$	-	63	-	
Turn - off Delay Time	t _{d(off)}	T _j = 175°C	-	159	-	ns
Fall Time	t _f	Inductive Load	-	62	-	
		$I_{\rm C} = 200$ A, $V_{\rm CC} = 520$ V				
Reverse Bias Safe Operating Area	RBSOA	$V_{P} = 650V, V_{GE} = 15V$	FU	LL SQUA	RE	-
		$R_{G} = 60\Omega, T_{j} = 175^{\circ}C$				

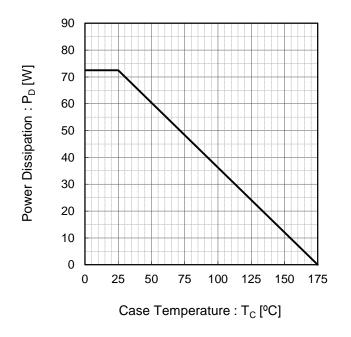


Fig.1 Power Dissipation vs. Case Temperature

Fig.2 Collector Current vs. Case Temperature

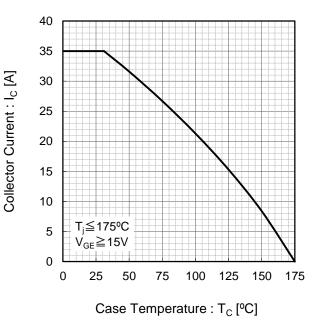
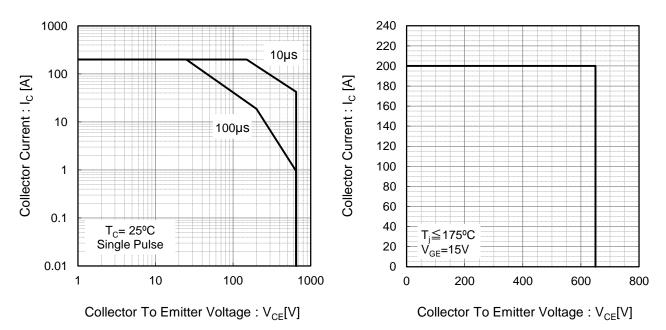


Fig.3 Forward Bias Safe Operating Area

Fig.4 Reverse Bias Safe Operating Area



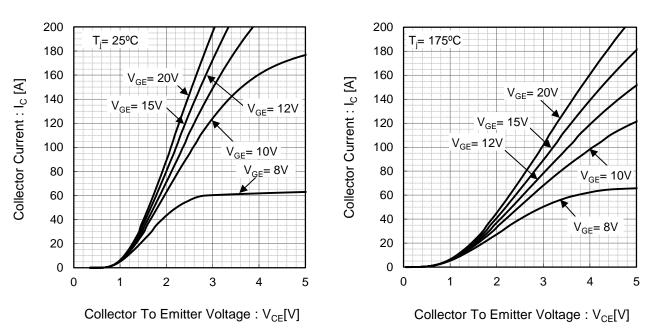
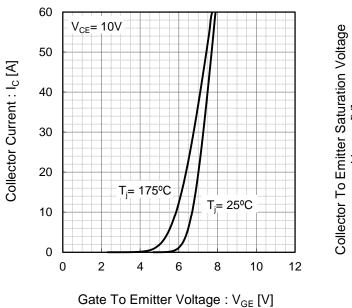


Fig.5 Typical Output Characteristics

Fig.7 Typical Transfer Characteristics

Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature

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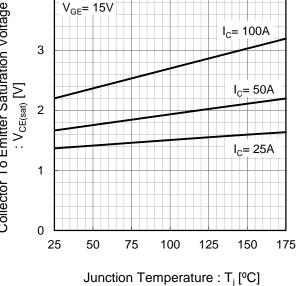


Fig.6 Typical Output Characteristics

Fig.10 Typical Collector To Emitter Saturation Voltage

•Electrical Characteristic Curves

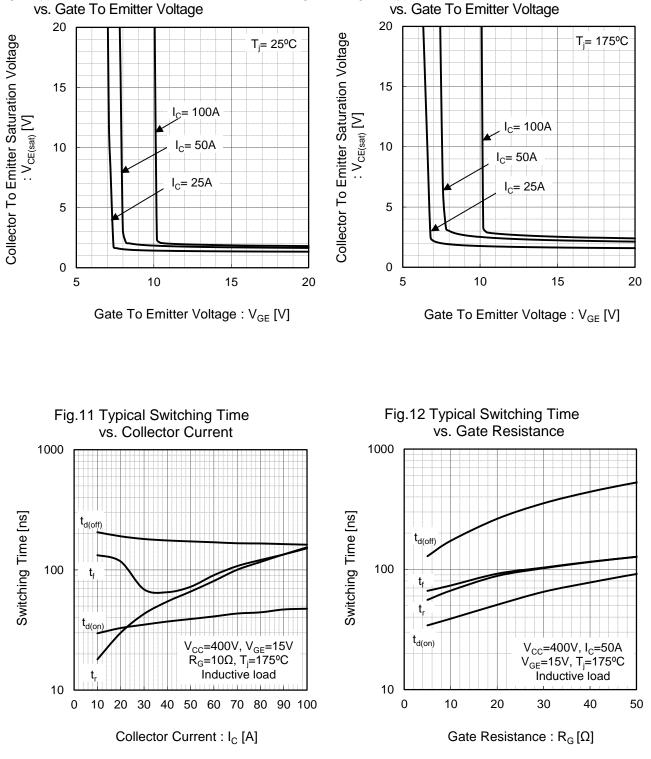
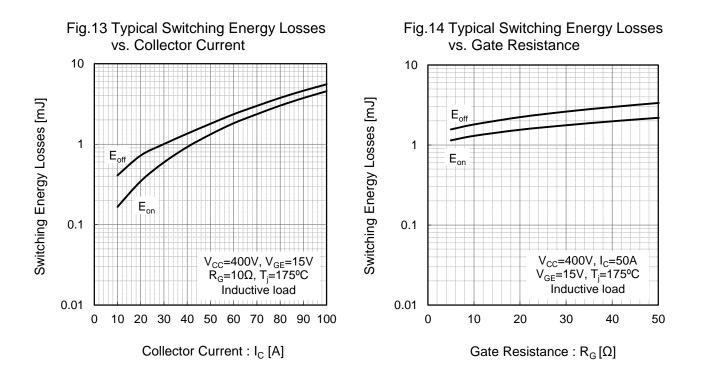
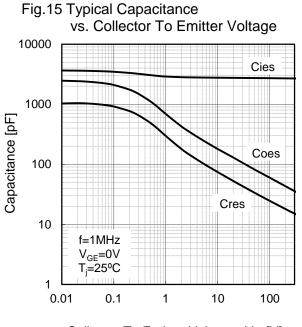


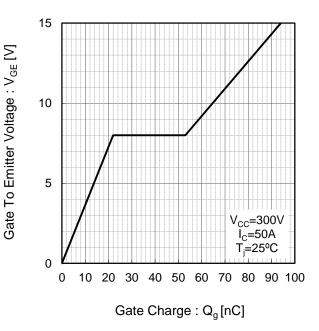
Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage





Collector To Emitter Voltage : V_{CE}[V]

Fig.16 Typical Gate Charge



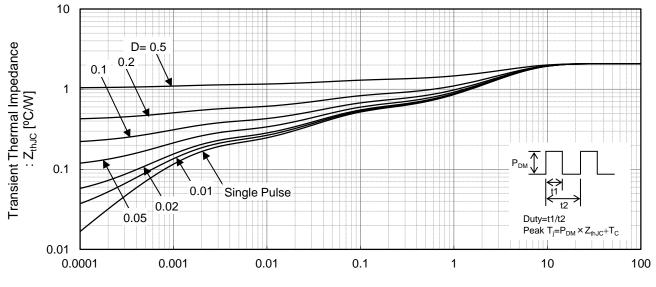


Fig.17 IGBT Transient Thermal Impedance

Pulse Width : t1[s]

●Inductive Load Switching Circuit and Waveform

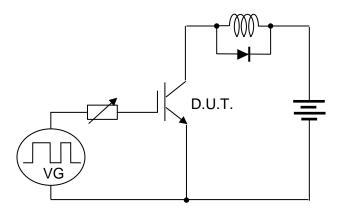
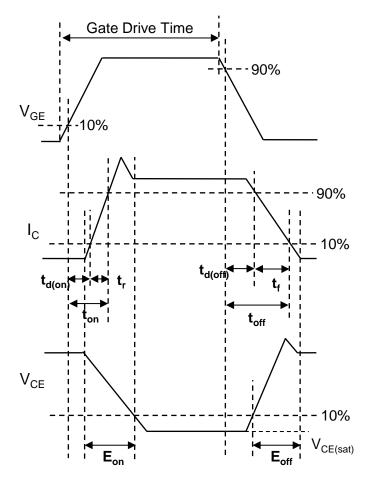


Fig.18 Inductive Load Circuit





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